

HiPerFET™ Power MOSFETs

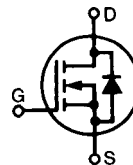
IXFH 80N085
IXFT 80N085

$V_{DSS} = 85\text{ V}$
 $I_{D25} = 80\text{ A}$
 $R_{DS(on)} = 9\text{ m}\Omega$

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt

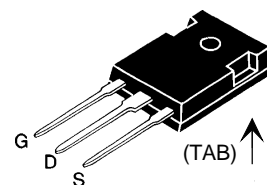
$t_{rr} \leq 200\text{ ns}$

Preliminary data sheet

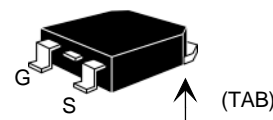


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	85	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	85	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	80	A
$I_{L(RMS)}$	Lead current limit	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	320	A
I_{AR}	$T_C = 25^\circ\text{C}$	80	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	mJ
E_{AS}		2.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 AD (IXFH)



TO-268 (IXFT) Case Style



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	85		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2.0		V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		50 μA
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			9 m Ω

Features

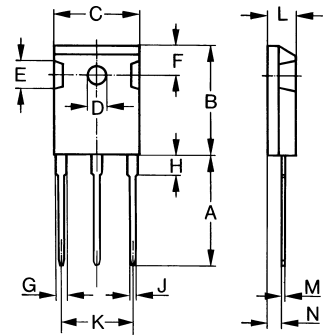
- International standard packages
- Low $R_{DS(on)}$
- Rated for unclamped Inductive load switching (UIS)
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	35	55	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4800	pF
C_{oss}			1675	pF
C_{rss}			590	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\ \Omega$ (External),		50	ns
t_r			75	ns
$t_{d(off)}$			95	ns
t_f			31	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		180	nC
Q_{gs}			42	nC
Q_{gd}			75	nC
R_{thJC}	(TO-247)			0.42 K/W
R_{thCK}			0.25	K/W

TO-247 AD (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			80 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			320 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		0.5	200 ns
Q_{RM}			6	μC
I_{RM}				A

TO-268AA (D ³ PAK)		Dim.		Millimeter		Inches	
		Min.	Max.	Min.	Max.	Min.	Max.
	A	4.9	5.1	.193	.201		
	A ₁	2.7	2.9	.106	.114		
	A ₂	.02	.25	.001	.010		
	b	1.15	1.45	.045	.057		
	b ₂	1.9	2.1	.75	.83		
	C	.4	.65	.016	.026		
	D	13.80	14.00	.543	.551		
	E	15.85	16.05	.624	.632		
	E ₁	13.3	13.6	.524	.535		
	e	5.45 BSC		.215 BSC			
	H	18.70	19.10	.736	.752		
	L	2.40	2.70	.094	.106		
	L ₁	1.20	1.40	.047	.055		
	L ₂	1.00	1.15	.039	.045		
	L ₃	0.25 BSC		.010 BSC			
	L ₄	3.80	4.10	.150	.161		

